	Туре	Hits	Search Text	DBs
1	IS&R	15	(("5008212") or ("5021121") or ("5102815") or ("5242532") or ("5242536") or ("5242536") or ("5441596") or ("5451290") or ("5474648") or ("5662770") or ("5843226") or ("5998302") or ("6083844") or ("6159794") or ("6162696")).PN.	USPAT
2	IS&R	1999	(438/629,636,637,639,640).CCLS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	1	substrate with ((Si silicon) and (Ge germanium) and (gallium adj nitride gan "GaN" "Ga N")) and DRAM and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	4764	striation\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	2	((438/629,636,637,639,640).CCL S.) and striation\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	144	striation\$1 and (438/\$ 257/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	0	substrate with ((Si silicon) and (Ge germanium) and (gallium adj nitride gan "GaN" "Ga N")) and (striation\$1 and (438/\$ 257/\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	8	substrate with ((Si silicon) and (Ge germanium)) and (striation\$1 and (438/\$ 257/\$))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	2	striation\$1 and (substrate\$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	18	substrate\$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide and (cd critical adj dimension\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	197	(gallium adj arsenide gan	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	0	substrate\$1 with ((Si silicon) and (Ge germanium)) and DRAM and oxide	JPO

	Time Stamp	Comments	Francis	
-	camp		Definition	Errors
1	2002/06/24 13:14			0
2	2002/06/24			0
3	2002/06/24			0
4	2002/06/24 13:54			0
5	2002/06/24 13:59			0
6	2002/06/24 14:06			0
7	2002/06/24 14:08			0
8	2002/06/24 14:09		,	0
9	2002/06/24 14:14			0
10	2002/06/24 14:18			0
11	2002/06/24 15:05			0
12	2002/06/24 14:29			0

-	Туре	Hits	Search Text	DBs
13	BRS	140	substrate\$1 with ((Si silicon)) and DRAM and oxide	JPO
14	BRS	1	substrate\$1 with ((Si silicon)) and DRAM and oxide and (anti adj reflect\$3 antireflect\$3 Arc Arl)	JPO
15	BRS	145	<pre>substrate\$1 with ((Si silicon)) and oxide and (anti adj reflect\$3 antireflect\$3 Arc Arl)</pre>	JPO
16	BRS	2	substrate\$1 with ((Si silicon)) and oxide and (anti adj reflect\$3 antireflect\$3 Arc Arl) and (memory dynamic)	JPO
17	BRS	18	(substrate\$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide) and (anti adj reflect\$3 antireflect\$3 Arc Arl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	2	striation\$1 and (substrate\$1 with ((Si silicon) and (Ge germanium) and (gallium adj arsenide gan "GaAs" "Ga As")) and DRAM and oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
13	2002/06/24 14:29			0
14	2002/06/24 14:31			0
15	2002/06/24 14:31			0
16	2002/06/24 14:31			0
17	2002/06/24 17:07			0
18	2002/06/24 17:07			0